

# Kei Sumita

## List of Publications by Year in descending order

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Version: 2024-02-01

14  
papers

70  
citations

1684188

5  
h-index

1588992

8  
g-index

14  
all docs

14  
docs citations

14  
times ranked

69  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effective Mobility Enhancement Through Asymmetric Strain Channels on Extremely Thin Body (100) GOI pMOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 25-30.	3.0	6
2	Optimum Channel Design of Extremely-Thin-Body nMOSFETs Utilizing Anisotropic Valley "Robust to Surface Roughness Scattering. IEEE Transactions on Electron Devices, 2022, 69, 2115-2121.	3.0	5
3	Electrical Properties of Ultra-Thin Body (111) Ge-On-Insulator n-Channel MOSFETs Fabricated by Smart-Cut Process. IEEE Journal of the Electron Devices Society, 2021, 9, 612-617.	2.1	3
4	Advanced CMOS technologies for ultra-low power logic and AI applications. , 2021, , .		2
5	Proposal and Experimental Demonstration of Ultrathin-Body (111) InAs-On-Insulator nMOSFETs With L Valley Conduction. IEEE Transactions on Electron Devices, 2021, 68, 2003-2009.	3.0	7
6	Evaluation of interface traps inside the conduction band of InAs-on-insulator nMOSFET by self-consistent Hall-QSCV method. Applied Physics Letters, 2021, 119, .	3.3	2
7	Optimum Design of Channel Material and Surface Orientation for Extremely-Thin-Body nMOSFETs under New Modeling of Surface Roughness Scattering. , 2021, , .		3
8	Influence of layer transfer and thermal annealing on the properties of InAs-On-Insulator films. Journal of Applied Physics, 2020, 128, .	2.5	4
9	Corrections to "Operation of (111) Ge-on-Insulator n-channel MOSFET Fabricated by Smart-Cut Technology" [Jul 20 985-988]. IEEE Electron Device Letters, 2020, 41, 1266-1266.	3.9	1
10	Operation of (111) Ge-on-Insulator n-Channel MOSFET Fabricated by Smart-Cut Technology. IEEE Electron Device Letters, 2020, 41, 985-988.	3.9	13
11	Effects of hydrogen ion implantation dose on physical and electrical properties of Ge-on-insulator layers fabricated by the smart-cut process. AIP Advances, 2020, 10, .	1.3	7
12	Accurate evaluation of specific contact resistivity between InAs/Ni-InAs alloy using a multi-sidewall transmission line method. Japanese Journal of Applied Physics, 2020, 59, SGG408.	1.5	5
13	Subband Engineering by Combination of Channel Thickness Scaling and (111) Surface Orientation in InAs-On-Insulator nMOSFETs. , 2020, , .		3
14	Fabrication of thin body InAs-on-insulator structures by Smart Cut method with H <sup>+</sup> implantation at room temperature. Japanese Journal of Applied Physics, 2019, 58, SBBA03.	1.5	9